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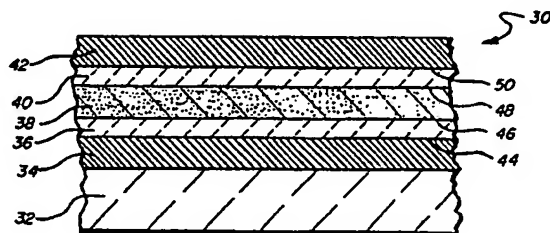
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54 **Thin film electrical devices with amorphous carbon electrodes and method of making same.**

57 Thin film electrical structures, such as threshold switching devices and phase change memory cells, preferably utilizing electrically stable, relatively inert, conductive electrodes including a non-single-crystal deposited film of carbon material, are disclosed. The film of carbon material, which preferably is amorphous and substantially pure, is disposed adjacent to a layer of active material such as an amorphous semiconductor, and serves to prevent undesired degradation of the active material, especially when the device is carrying appreciable current in its on-state. A method of making such structures with high quality interfaces between the semiconductor layer and the conductive carbon barrier layers adjacent thereto by successively depositing such layers in a continuously maintained partial vacuum is disclosed. The method may include a step performed in the vacuum for hermetically sealing all of, or at least the electrically switchable portion of, the active layer against subsequent contamination. Thin film structures suitable for threshold switching or memory

applications and employing insulating pores having substantially sloped side walls are also disclosed.



**FIG. 1**

**EP 0 269 225 A3**



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# EUROPEAN SEARCH REPORT

Application Number

EP 87 30 8723

DOCUMENTS CONSIDERED TO BE RELEVANT			
Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int. Cl. 4)
A	US-A-4 433 342 (V. N. PATEL et al.) * the whole document * ---	1-14	H 01 L 45/00 H 01 L 29/40 H 01 L 21/285
A	WO-A-8 301 153 (INTERFACES) * the whole document * ---	1-14	
A	US-A-3 886 577 (W. D. BUCKLEY) * the whole document * -----	1-14	
			TECHNICAL FIELDS SEARCHED (Int. Cl. 4)
			H 01 L H 02 H
The present search report has been drawn up for all claims			
Place of search BERLIN		Date of completion of the search 18-06-1989	Examiner ROUSSEL A T
<b>CATEGORY OF CITED DOCUMENTS</b>			
X : particularly relevant if taken alone Y : particularly relevant if combined with another document of the same category A : technological background O : non-written disclosure P : intermediate document		T : theory or principle underlying the invention E : earlier patent document, but published on, or after the filing date D : document cited in the application L : document cited for other reasons ----- & : member of the same patent family, corresponding document	